

EE105 - Fall 2005

Microelectronic Devices and Circuits

Lecture 6

**Currents in PN Junction
MOS Capacitor**

Announcements

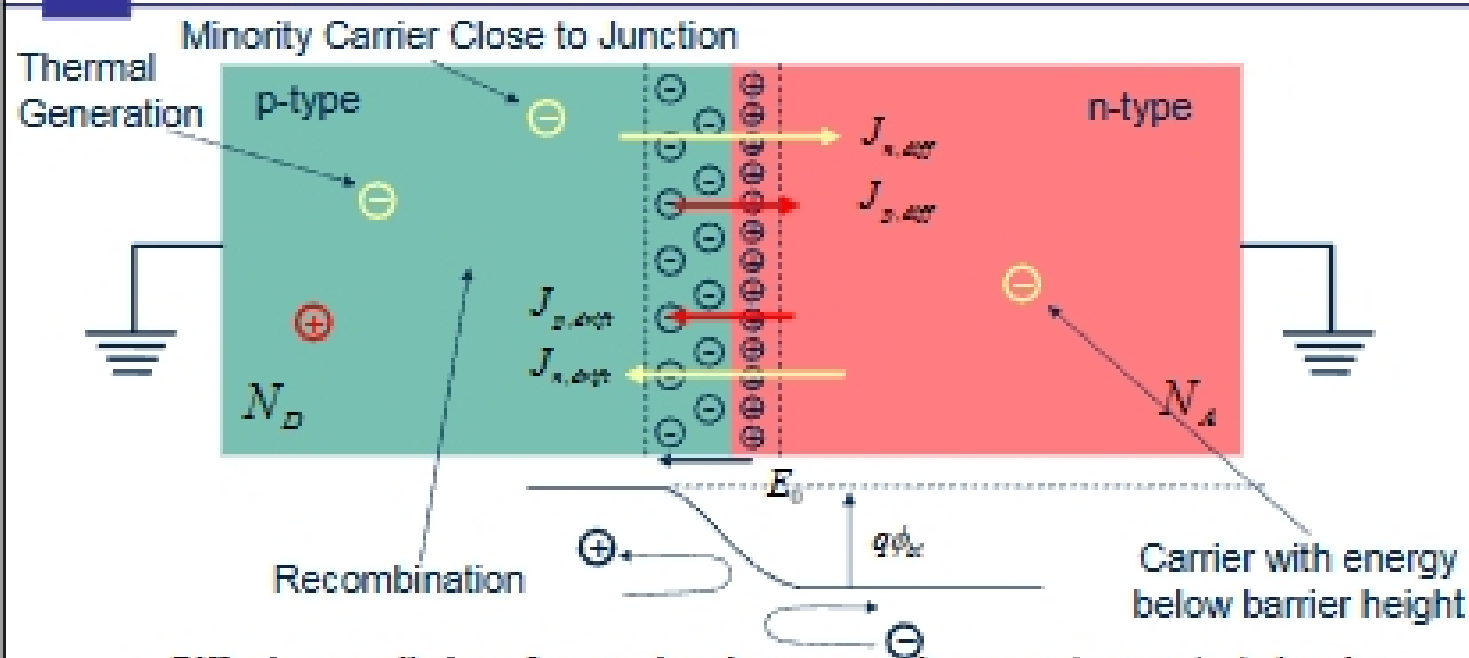
- › **Homework 3, due next week**
- › **Reading: Chapter 3 (3.7-3.9)**

Lecture Material

- › Last lecture
 - › PN junction
 - › Diode capacitance
- › This lecture
 - › Diode currents
 - › MOS capacitor

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Diode under Thermal Equilibrium

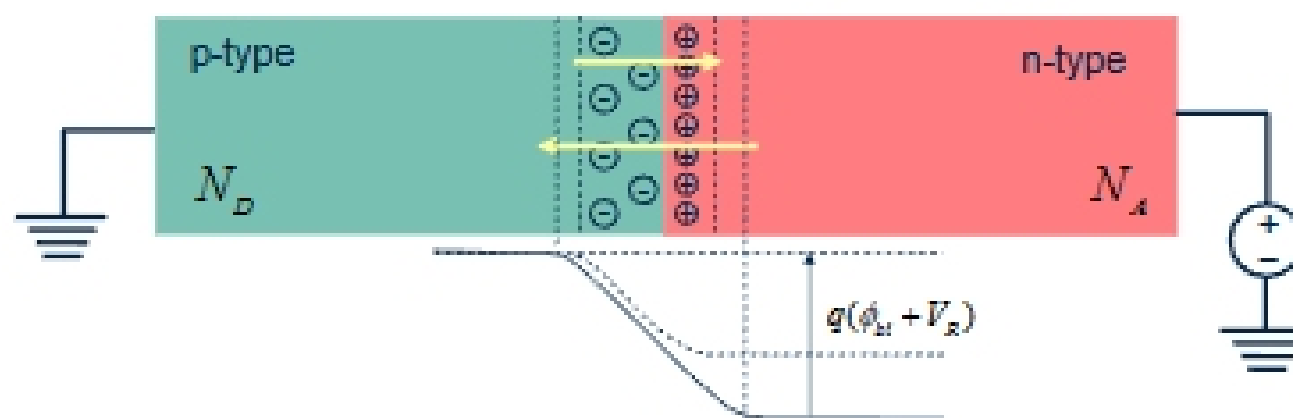


- › Diffusion small since few carriers have enough energy to penetrate barrier
- › Drift current is small since minority carriers are few and far between: Only minority carriers generated within a diffusion length can contribute current
- › Important Point: Minority drift current independent of barrier!
- › Diffusion current strong (exponential) function of barrier

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Reverse Bias

- Reverse Bias causes an increase in barrier to diffusion
- Diffusion current is reduced exponentially

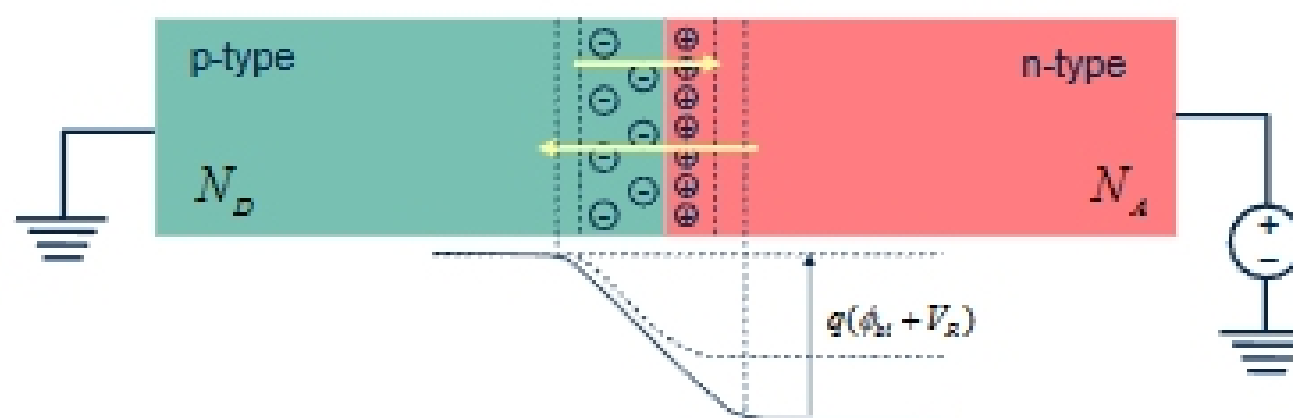


- Drift current does not change
- Net result: Small reverse current

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Forward Bias

- Forward bias causes an exponential increase in the number of carriers with sufficient energy to penetrate barrier
- Diffusion current **increases** exponentially



- Drift current does not change
- Net result: Large forward current

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